

VPD ICP-MS METHOD DETECTION LIMITS AND RECOVERIES FOR TRACE METALS CONTAMINATION ANALYSIS OF SILICON WAFERS

200_{mm}

SILICON WAFERS

VPD ICP-MS METHOD DETECTION LIMITS, ATOMS/CM²

Method detection limits for WSS, DFS and BSE ICP-MS vary depending on techniques.

Aluminum	Al	3e9
Antimony	Sb	2e7
Arsenic	As	5e9
Barium	Ba	2e7
Beryllium	Be	2e9
Bismuth	Bi	1e7
Boron	B	5e10
Cadmium	Cd	3e7
Calcium	Ca	3e9
Cesium	Cs	5e7
Chromium	Cr	6e8
Cobalt	Co	5e8
Copper	Cu	2e8
Gallium	Ga	3e7
Germanium	Ge	1e8
Hafnium	Hf	5e7
Iron	Fe	1e9
Lanthanum	La	2e7
Lead	Pb	3e7
Lithium	Li	5e8
Magnesium	Mg	1e9
Manganese	Mn	3e8
Molybdenum	Mo	2e7
Niobium	Nb	1e8
Nickel	Ni	5e8
Potassium	K	2e9
Rubidium	Rb	1e9
Sodium	Na	2e9
Strontium	Sr	1e8
Tantalum	Ta	3e7
Thallium	Tl	5e7
Thorium	Th	5e7
Tin	Sn	3e8
Titanium	Ti	5e8
Tungsten	W	1e7
Uranium	U	5e8
Vanadium	V	1e8
Yttrium	Y	3e8
Zinc	Zn	5e8
Zirconium	Zr	1e8

Vapor Phase Decomposition (VPD) Inductively Coupled Plasma Mass Spectrometry (ICP-MS) is the most widely used analytical technique to monitor trace metals of bare wafers and wafers with silicon oxide or silicon nitride film. Based on this technique, ChemTrace has introduced additional methods of analysis that include Wafer Surface Scan (WSS) ICP-MS, Direct Film Stripping (DFS) ICP-MS and Bulk Silicon Etch (BSE) ICP-MS. These new techniques allow for monitoring of a broader variety of process films, including metal films, low-k and high-k dielectric films, SiGe and polysilicon films.

Legends:

- Excellent Recovery (100% -85%)
- Good Recovery (84% -70%)
- Low Recovery (<70%)
- No Data Yet
- Not Analyzed

GROUP IA

1	² S _{1/2}	H Hydrogen 1.00794
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IIA

3	² S _{1/2}	Li Lithium 6.941
4	¹ S ₀	Be Beryllium 9.01218

11	² S _{1/2}	Na Sodium 22.98977
12	¹ S ₀	Mg Magnesium 24.3050

IIIB

IVB

VB

VIB

VIIB

VIIIB

IB

IIB

19	² S _{1/2}	K Potassium 39.0983
20	¹ S ₀	Ca Calcium 40.078

21	² D _{3/2}	Sc Scandium 44.95591
22	³ F ₂	Ti Titanium 47.867

23	⁴ F _{3/2}	V Vanadium 50.9415
24	³ S ₂	Cr Chromium 51.9961

25	⁴ S _{3/2}	Mn Manganese 54.93805
26	⁵ D ₄	Fe Iron 55.845

27	⁴ F _{7/2}	Co Cobalt 58.93320
28	³ F ₄	Ni Nickel 58.6934

29	² S _{1/2}	Cu Copper 63.546
30	¹ S ₀	Zn Zinc 65.39

31	² P _{1/2}	Ga Gallium 69.723
32	³ P ₀	Ge Germanium 72.61

33	⁴ S _{3/2}	As Arsenic 74.92160
34	³ P ₂	Se Selenium 78.96

35	² P _{3/2}	Br Bromine 79.904
36	¹ S ₀	Kr Krypton 83.80

37	² S _{1/2}	Rb Rubidium 85.4678
38	¹ S ₀	Sr Strontium 87.62

39	² D _{3/2}	Y Yttrium 88.90585
40	³ F ₂	Zr Zirconium 91.224

41	⁶ D _{1/2}	Nb Niobium 92.90638
42	⁷ S ₃	Mo Molybdenum 95.94

43	⁶ S _{1/2}	Tc Technetium (98)
44	³ F ₅	Ru Ruthenium 101.07

45	⁴ F _{9/2}	Rh Rhodium 102.90550
46	¹ S ₀	Pd Palladium 106.42

47	² S _{1/2}	Ag Silver 107.8682
48	¹ S ₀	Cd Cadmium 112.411

49	² P _{1/2}	In Indium 114.818
50	³ P ₀	Sn Tin 118.710

51	⁴ S _{3/2}	Sb Antimony 121.760
52	³ P ₂	Te Tellurium 127.60

53	² P _{3/2}	I Iodine 126.90447
54	¹ S ₀	Xe Xenon 131.29

55	² S _{1/2}	Cs Cesium 132.90545
56	¹ S ₀	Ba Barium 137.327

72	³ F ₂	Hf Hafnium 178.49
73	⁴ F _{3/2}	Ta Tantalum 180.9479

74	³ D ₀	W Tungsten 183.84
75	⁶ S _{1/2}	Re Rhenium 186.207

76	³ D ₄	Os Osmium 190.23
77	⁴ F _{9/2}	Ir Iridium 192.217

78	³ D ₃	Pt Platinum 195.078
79	² S _{1/2}	Au Gold 196.96655

80	¹ S ₀	Hg Mercury 200.59
81	² P _{1/2}	Tl Thallium 204.3833

82	³ P ₀	Pb Lead 207.2
83	⁴ S _{3/2}	Bi Bismuth 208.98038

84	⁴ P ₂	Po Polonium (209)
85	² P _{3/2}	At Astatine (210)

86	¹ S ₀	Rn Radon (222)
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87	² S _{1/2}	Fr Francium (223)
88	¹ S ₀	Ra Radium (226)

104	³ F _{2,1}	Rt Rutherfordium (261)
105		Db Dubnium (262)

106		Sg Seaborgium (263)
107		Bh Bohrium (264)

108		Hs Hassium (265)
109		Mt Meitnerium (268)

110		Uun Ununnilium (272)
111		Uuu Unununium (272)

112		Uub Ununbium (272)
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57	² D _{3/2}	La Lanthanum 138.9055
58	¹ G _{5/2}	Ce Cerium 140.116

59	⁴ F _{5/2}	Pr Praseodymium 140.90765
60	⁵ I ₄	Nd Neodymium 144.24

61	⁶ H _{5/2}	Pm Promethium (145)
62	⁷ F ₀	Sm Samarium 150.36

63	⁸ S _{5/2}	Eu Europium 151.964
64	⁹ D ₂	Gd Gadolinium 157.25

65	⁶ H _{13/2}	Tb Terbium 158.92534
66	⁵ I ₈	Dy Dysprosium 162.50

67	⁴ F _{15/2}	Ho Holmium 164.93032
68	³ H ₆	Er Erbium 167.26

69	² F _{7/2}	Tm Thulium 168.93421
70	¹ S ₀	Yb Ytterbium 173.04

71	² D _{3/2}	Lu Lutetium 174.967
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89	² D _{3/2}	Ac Actinium (227)
90	³ F ₂	Th Thorium 232.0381

91	⁴ K _{11/2}	Pa Protactinium 231.03588
92	⁵ L ₀	U Uranium 238.0289

93	⁶ L _{11/2}	Np Neptunium (237)
94	⁷ F ₀	Pu Plutonium (244)

95	⁸ S _{5/2}	Am Americium (243)
96	⁹ D ₂	Cm Curium (247)

97	⁶ H _{13/2}	Bk Berkelium (247)
98	⁵ I ₈	Cf Californium (251)

99	⁴ F _{15/2}	Es Einsteinium (252)
100	³ H ₆	Fm Fermium (257)

101	² F _{7/2}	Md Mendelevium (258)
102	¹ S ₀	No Nobelium (259)

103	² F _{11/2}	Lr Lawrencium (262)
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Atomic Number	58
Ground-state Level	¹ G _{5/2}
Symbol	Ce
Name	Cerium
Atomic Weight	140.116
Method Detection Limit (atoms/cm ²)	2e7
Percentage Recovery on Si wafers (%)	91

VPD ICP-MS METHOD DETECTION LIMITS AND RECOVERIES

FOR TRACE METALS CONTAMINATION ANALYSIS OF SILICON WAFERS

300mm

SILICON WAFERS

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Cobalt	Co	3e8
Copper	Cu	1e8
Gallium	Ga	2e7
Germanium	Ge	5e7
Hafnium	Hf	3e7
Iron	Fe	5e8
Lanthanum	La	1e7
Lead	Pb	2e7
Lithium	Li	3e8
Magnesium	Mg	5e8
Manganese	Mn	1e8
Molybdenum	Mo	1e7
Niobium	Nb	5e7
Nickel	Ni	3e8
Potassium	K	1e9
Rubidium	Rb	5e8
Sodium	Na	1e9
Strontium	Sr	5e7
Tantalum	Ta	2e7
Thallium	Tl	3e7
Thorium	Th	3e7
Tin	Sn	1e8
Titanium	Ti	3e8
Tungsten	W	5e6
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Vanadium	V	5e7
Yttrium	Y	1e8
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19 ² S _{1/2} K Potassium 39.0983 1e9 100	20 ¹ S ₀ Ca Calcium 40.078 1e9 100
37 ² S _{1/2} Rb Rubidium 85.4678 5e8 100	38 ¹ S ₀ Sr Strontium 87.62 5e7 100
55 ² S _{1/2} Cs Cesium 132.90545 3e7 100	56 ¹ S ₀ Ba Barium 137.327 8e6 100
87 ² S _{1/2} Fr Francium (223)	88 ¹ S ₀ Ra Radium (226)

IIA

IIIB

IVB

VB

VIB

VIIA

VIIIB

IB

IIB

IIIA

IVA

VA

VIA

VIIA

VIIIA

5 ² P _{1/2} B Boron 10.811 2e10 100	6 ³ P ₀ C Carbon 12.0107	7 ⁴ S _{3/2} N Nitrogen 14.00674	8 ³ P ₂ O Oxygen 15.9994	9 ² P _{3/2} F Fluorine 18.99840	10 ¹ S ₀ Ne Neon 20.1797
13 ² P _{1/2} Al Aluminum 26.98154 1e9 100	14 ³ P ₀ Si Silicon 28.0855	15 ⁴ S _{3/2} P Phosphorus 30.97376 5e10 99	16 ³ P ₂ S Sulfur 32.066	17 ² P _{3/2} Cl Chlorine 35.4527	18 ¹ S ₀ Ar Argon 39.948
31 ² P _{1/2} Ga Gallium 69.723	32 ³ P ₀ Ge Germanium 72.61	33 ⁴ S _{3/2} As Arsenic 74.92160	34 ³ P ₂ Se Selenium 78.96	35 ² P _{3/2} Br Bromine 79.904	36 ¹ S ₀ Kr Krypton 83.80
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81 ² P _{1/2} Tl Thallium 204.3833 3e7 100	82 ³ P ₀ Pb Lead 207.2 2e7 100	83 ⁴ S _{3/2} Bi Bismuth 208.98038 5e6 100	84 ⁴ P ₂ Po Polonium (209)	85 ² P _{3/2} At Astatine (210)	86 ¹ S ₀ Rn Radon (222)
109 Mt Meitnerium (268)	110 Uun Ununnilium (272)	111 Uuu Unununium (272)	112 Uub Ununbium		

Atomic Number	58
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Name	Cerium
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89 ² D _{3/2} Ac Actinium (227)	90 ³ F ₂ Th Thorium 232.0381 3e7 84	91 ⁴ K _{11/2} Pa Protactinium 231.03588	92 ⁵ L ₀ U Uranium 238.0289 3e8 100	93 ⁶ L _{11/2} Np Neptunium (237)	94 ⁷ F ₀ Pu Plutonium (244)	95 ⁸ S _{7/2} Am Americium (243)	96 ⁹ D ₂ Cm Curium (247)	97 ⁶ H _{5/2} Bk Berkelium (247)	98 ⁵ I ₈ Cf Californium (251)	99 ⁴ F _{9/2} Es Einsteinium (252)	100 ³ H ₆ Fm Fermium (257)	101 ² F _{7/2} Md Mendelevium (258)	102 ¹ S ₀ No Nobelium (259)	103 ² F _{7/2} Lr Lawrencium (262)